

Title (en)
PROCESS FOR PREPARATION OF POLYCRYSTALLINE SILICON

Title (de)
VERFAHREN ZUR HERSTELLUNG VON POLYKRISTALLINEM SILIZIUM

Title (fr)
PROCEDE DE PREPARATION DE SILICIUM POLYCRISTALLIN

Publication
EP 1392601 A1 20040303 (EN)

Application
EP 02737219 A 20020523

Priority
• US 0216754 W 20020523
• US 87767401 A 20010608

Abstract (en)
[origin: US2002187096A1] A process for preparing polycrystalline silicon comprising the steps of (A) reacting trichlorosilane with hydrogen thereby forming silicon and an effluent mixture comprising tetrachlorosilane and disilane described by formula $H_nCl_{6-n}Si_2$ where n is a value of 0 to 6 and (B) co-feeding the effluent mixture and hydrogen to a reactor at a temperature within a range of about 600° C. to 1200° C. thereby effecting hydrogenation of the tetrachlorosilane and conversion of the disilane to monosilanes.

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IPC 8 full level
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Cited by
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